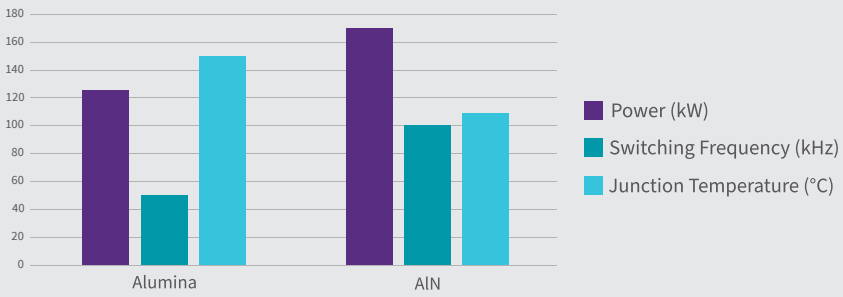
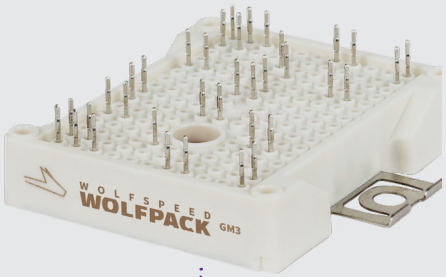
WOLFSPEED WOLFPACK™ GM3 SILICON CARBIDE POWER MODULES WITH ALUMINUM NITRIDE SUBSTRATE

DELIVERING THE INDUSTRY'S HIGHEST POWER DENSITY IN ITS CLASS FOR UNSURPASSED EFFICIENCY

Aluminum nitride (AlN) can offer large performance impacts with a relatively low cost increase. With 7X higher thermal conductivity compared to Alumina, the impacts can easily be understood: Dramatically reduces thermal resistance, lowers junction temperature for given loss, enhances power cycling lifetime for given losses, enables higher utilization of Silicon Carbide performance.





>50% reduction in R_{th}

PRODUCT PORTFOLIO

Platform	$R_{DS(on)}$ at 25°C	Product SKU	Description	Blocking Voltage
G PLATFORM std. 56.7mm	6 mΩ	CAB006A12GM3	Half-Bridge, AlN Substrate	1200 V
G PLATFORM std. 56.7mm	8 mΩ	CAB008A12GM3	Half-Bridge, AlN Substrate	1200 V

FEATURES

- High performance Aluminum Nitride (AlN) substrate
- Leading Silicon Carbide MOSFET technology in an industry standard form factor
- Highest current rated topologies commercially available
- Built in NTC
- Press fit connections

BENEFITS

- Reduces thermal resistance by over 50%
- Maximum power density
- Ease of layout and assembly
- System scalability and reliability
- Simpler cooling systems and smaller systems

APPLICATIONS

- Electronic Vehicle Chargers
- Solar
- High-Efficiency Converters/Inverters
- Motor & Traction Drives
- Smart Grid/Grid-Tied Distributed Generation

TO LEARN MORE, VISIT US AT **WOLFSPEED.COM**